

Continental Device India Limited

An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company





SOT-23 Formed SMD Package

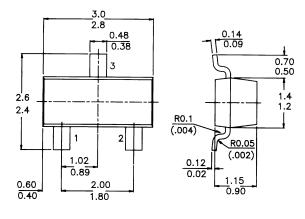
CMBT918

VHF/UHF TRANSISTOR

N-P-N transistor

Marking CMBT918 = 3B

PACKAGE OUTLINE DETAILS ALL DIMENSIONS IN mm



Pin configuration

1 = BASE

2 = EMITTER

3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	3	V
Collector current (d.c.)	$-I_C$	max.	350	mA
Total power dissipation at $T_{amb} = 25^{\circ}C$	P_{tot}	max	225	mW
D.C. current gain				
$-I_C = 3 \text{ mA}; -V_{CE} = 1 \text{ V}$	h_{FF}	min.	20	

RATINGS (at $T_A = 25$ °C unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	3	V
Collector current (d.c.)	$-I_C$	max.	350	mA

CMBT918

Total power dissipation at $T_{amb} = 25^{\circ}C$ Storage temperature Junction temperature	P _{tot} T _{stg} Tj	max -55 to max.	225 +150 150	mW ° C ° C
THERMAL CHARACTERISTICS	-,		100	
$T_j = P (R_{th j-t} + R_{th s-a}) + T_{amb}$				
Thermal resistance				
from junction to ambient	$R_{th\ j-a}$		556	°C/mW
CHARACTERISTICS (at $T_A = 25^{\circ}C$ unless otherwise	e specified)			
Collector-emitter breakdown voltage				
$-I_C = 3 \text{ mA}; -I_B = 0$	-V(BR)CEO	min.	15	V
Collector-base breakdown voltage				
$-I_C = 1 \mu A; -I_E = 0$	-V _(BR) CBO	min.	<i>30</i>	V
Emitter-base breakdown voltage				
$-I_E = 10 \ \mu A; -I_C = 0$	$-V_{(BR)EBO}$	min.	3	V
Collector cut-off current				
$-V_{CB} = 15 V; -I_{E} = 0$	$-I_{CBO}$	max.	<i>50</i>	nΑ
Output capacitance at $f = 1 MHz$				
$-V_{CB} = 10 \ V; \ I_E = 0$	C_c	max.	1.7	pF
Input capacitance at $f = 1$ MHz				
$-V_{EB} = 0.5 V; I_{C} = 0$	C_e	max.	2	pF
Saturation voltages	* 7		0.4	• •
$-I_C = 10 \text{ mA}; -I_B = 1 \text{ mA}$	-V _{CEsat}	max.	0.4	V
	-V _{BEsat}	max.	1	V
D.C. current gain	_			
$-I_C = 3 \text{ mA; } -V_{CE} = 1 \text{ V}$	h_{FE}	min.	20	
Noise figure at $R_S = 50 \Omega$				
$-I_C = 1 \text{ mA; } -V_{CE} = 6 \text{ V}$				15
f = 60 MHz	NF	max.	6	dB
Transition frequency				
$V_{CE} = 10 \ V; I_{C} = 4 \ mA; f = 100 \ MHz$	f_T	min.	600	MHz

Customer Notes

Disclaimer

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